REVISIONS			
LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED

REV																			
SHEET																			
REV																			
SHEET	15	16	17	18	19	20	21	22											

REV STATUS OF SHEETS	REV														
	SHEET	1	2	3	4	5	6	7	8	9	10	11	12	13	14

PMIC N/A

PREPARED BY
Joseph A. Kerby

DEFENSE SUPPLY CENTER COLUMBUS

COLUMBUS, OHIO 43216

STANDARD MICROCIRCUIT DRAWING

CHECKED BY
Charles F. Saffle, Jr.

THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE

APPROVED BY
Monica L. Poelking

MICROCIRCUIT, DIGITAL, ADVANCED BIPOLAR CMOS, 18-BIT UNIVERSAL BUS TRANSCEIVER WITH THREE-STATE OUTPUTS AND B-PORT EQUIVALENT 25 OHM OUTPUT SERIES RESISTORS, MONOLITHIC SILICON

DRAWING APPROVAL DATE
98-06-24

AMSC N/A

REVISION LEVEL

SIZE	CAGE CODE	
A	67268	5962-98593

SHEET 1 OF 22

DSCC FORM 2233
APR 97

5962-E423-98

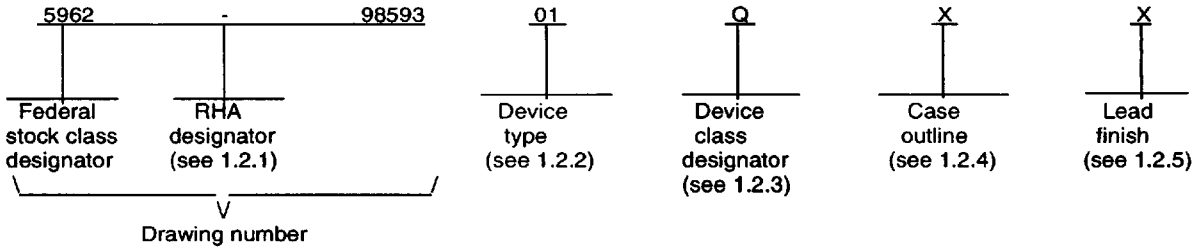
DISTRIBUTION STATEMENT A. Approved for public release; distribution is unlimited.

9004708 0039629 932

1. SCOPE

1.1 Scope. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.

1.2 PIN. The PIN is as shown in the following example:



1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 Device type(s). The device type(s) identify the circuit function as follows:

Device type	Generic number	Circuit function
01	54ABT162601	18-Bit Universal Bus Transceiver with three-state outputs and B-port equivalent 25 Ohm output series resistors.

1.2.3 Device class designator. The device class designator is a single letter identifying the product assurance level as follows:

Device class	Device requirements documentation
M	Vendor self-certification to the requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A
Q or V	Certification and qualification to MIL-PRF-38535

1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	Terminals	Package style
X	GDFP1-F56	56	Flat pack

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

1.3 Absolute maximum ratings. 1/ 2/ 3/

Supply voltage range (V_{CC})	-0.5 V dc to +7.0 V dc
DC input voltage range (V_{IN}),(except I/O ports)	-0.5 V dc to +7.0 V dc 4/
DC output voltage range in the high or power-off state (V_{OUT})	-0.5 V dc to 5.5 V dc 4/
Current into any output in the low state (I_{OL}):	
A port	96 mA
B port	30 mA
DC input clamp current (I_{IK}) (V_{IN} < 0.0)	-18 mA
DC output clamp current (I_{OK}) (V_{OUT} < 0.0)	-50 mA
Maximum power dissipation at T_A = +55°C (in still air) (P_D)	673 mW 5/
Storage temperature range (T_{STG})	-65°C to +150°C
Lead temperature (soldering, 10 seconds)	+300°C
Thermal resistance, junction-to-case (θ_{JC})	See MIL-STD-1835
Junction temperature (T_J)	+150°C

1.4 Recommended operating conditions. 2/ 3/ 6/

Supply voltage range (V_{CC})	+4.5 V dc to +5.5 V dc
Input voltage range (V_{IN})	0.0 V dc to V_{CC}
Minimum High level input voltage (V_{IH})	+2.0 V
Maximum Low level input voltage (V_{IL})	+0.8V
Maximum High level output current (I_{OH}):	
A port	-24 mA
B port	-12 mA
Maximum Low level output current (I_{OL}):	
A port	+48 mA
B port	+12 mA
Maximum input transition rise or fall rate ($\Delta t / \Delta V$) (outputs enabled)	10 ns/V
Minimum power-up ramp rate ($\Delta t/\Delta V_{CC}$)	200 µs/V
Operating free-air temperature (T_A)	-55°C to +125°C

1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.
2/ Unless otherwise noted, all voltages are referenced to GND.
3/ The limits for the parameters specified herein shall apply over the full specified V_{CC} range and case temperature range of -55°C to +125°C.
4/ The input and output negative-voltage ratings may be exceeded provided that the input and output clamp-current ratings are observed.
5/ Power dissipation values are derived using the formula $Pd = V_{CC}I_{CC} + nV_{OL}I_{OL}$, where V_{CC} and I_{OL} are as specified in 1.3 above, I_{CC} and V_{OL} are as specified in Table 1 herein, and "n" represents the total number of outputs.
6/ Unused pins (input or I / O) must be held high or low to prevent them from floating.

2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation.

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

STANDARDS

DEPARTMENT OF DEFENSE

MIL-STD-883 - Test Methods and Procedures for Microelectronics.
MIL-STD-973 - Configuration Management.
MIL-STD-1835 - Microcircuit Case Outlines.

HANDBOOKS

DEPARTMENT OF DEFENSE

MIL-HDBK-103 - List of Standard Microcircuit Drawings (SMD's).
MIL-HDBK-780 - Standard Microcircuit Drawings.

(Unless otherwise indicated, copies of the specification, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.

3.2.1 Case outlines. The case outlines shall be in accordance with 1.2.4 herein.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.

3.2.3 Truth table. The truth table shall be as specified on figure 2.

3.2.4 Logic diagram. The logic diagram shall be as specified on figure 3.

3.2.5 Ground bounce test circuit and waveforms. The ground bounce test circuit and waveforms shall be as specified on figure 4.

3.2.6 Switching waveforms and test circuit. The switching waveforms and test circuit shall be as specified on figure 5.

3.2.7 Radiation exposure circuit. The radiation exposure circuit shall be as specified when available.

3.3 Electrical performance characteristics and postirradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full case operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.

3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-HDBK-103. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.

3.5.1 Certification/compliance mark. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.

3.6 Certificate of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.

3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

3.8 Notification of change for device class M. For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-973.

3.9 Verification and review for device class M. For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 Microcircuit group assignment for device class M. Device class M devices covered by this drawing shall be in microcircuit group number 127 (see MIL-PRF-38535, appendix A).

TABLE I. Electrical performance characteristics.

Test and MIL-STD-883 test method 1/	Symbol	Test conditions 2/ -55°C ≤ T_C ≤ +125°C +4.5 V ≤ VCC ≤ +5.5 V unless otherwise specified		V_{CC}	Group A subgroups	Limits 3/		Unit
						Min	Max	
Input clamp voltage	V_{IK}	I_{IN} = -18 mA		4.5 V	1, 2, 3		-1.2	V
High level output voltage 3006	V_{OH} A port	For all inputs affecting output under test, V_{IN} = 2.0 V or 0.8 V For all other inputs, V_{IN} = V_{CC} or GND	I_{OH} = -3 mA	4.5 V	1, 2, 3	2.5		V
				5.0 V		3.0		
			I_{OH} = -24 mA	4.5 V		2.0		
	V_{OH} B port		I_{OH} = -1 mA	4.5 V	1	3.35		
				5.0 V		3.85		
				4.5 V	2, 3	3.3		
				5.0 V		3.8		
			I_{OH} = -3 mA	4.5 V	1	3.1		
					2, 3	3.0		
			I_{OH} = -12 mA	4.5 V	1	2.6		
Low level output voltage 3007	V_{OL} A port	For all inputs affecting output under test, V_{IN} = 2.0 V or 0.8 V For all other inputs, V_{IN} = V_{CC} or GND	I_{OL} = 48 mA	4.5 V	1, 2, 3		0.55	V
	V_{OL} B port		I_{OL} = 12 mA	4,5 V			0.8	
Input current high 3010	I_{IH} 4/	For input under test, V_{IN} = V_{CC}	Control Inputs	0.0 V and 5.5 V	1, 2, 3		1.0	µA
			A or B ports	2.1 V and 5.5 V			20.0	
Input current low 3009	I_{IL} 4/	For input under test, V_{IN} = 0.0 V	Control Inputs	0.0 V and 5.5 V	1, 2, 3		-1.0	µA
			A or B ports	2.1 V and 5.5 V			-20.0	

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test conditions 2/ $-55°C \le T_C \le +125°C$ $+4.5\ V \le VCC \le +5.5\ V$ unless otherwise specified	V_{CC}	Group A subgroups	Limits 3/		Unit
					Min	Max	
Three-state output current at power up condition	I_{OZPU} 5/	For output under test, V_{OUT} = 0.5 V to 2.7 V $\overline{OE}$ = 2.0 V or 0.8 V	0.0 V and 2.1 V	1, 2, 3		±50.0	µA
Three-state output current at power down condition	I_{OZPD} 5/	For output under test, V_{OUT} = 0.5 V to 2.7 V $\overline{OE}$ = 2.0 V or 0.8 V	2.1 V and 0.0 V	1, 2, 3		±50.0	µA
Three-state output leakage current high 3021	I_{OZH} 6/	For output under test, V_{OUT} = 2.7 V $\overline{OE} \ge$ 2.0 V	2.1 V and 5.5 V	1, 2, 3		10.0	µA
Three-state output leakage current low 3020	I_{OZL} 6/	For output under test, V_{OUT} = 0.5 V $\overline{OE} \ge$ 2.0 V	2.1 V and 5.5 V	1, 2, 3		-10.0	µA
High-state leakage current	I_{CEX}	For output under test, V_{OUT} = 5.5 V Outputs High	5.5 V	1,2,3		50.0	µA
Output current 3011	I_{OUT} A port 7/	V_{OUT} = 2.5 V	5.5 V	1, 2, 3	-50.0	-180.0	mA
	I_{OUT} B port 7/				-25.0	-100.0	
Quiescent supply current, outputs high 3005	I_{CCH}	For all inputs, $V_{IN} = V_{CC}$ or GND I_{OUT} = 0.0 A A or B ports	5.5 V	1, 2, 3		3.0	mA
Quiescent supply current, outputs low 3005	I_{CCL}		5.5 V	1, 2, 3		36.0	
Quiescent supply current, outputs disabled 3005	I_{CCZ}		5.5 V	1, 2, 3		3.0	

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test conditions 2/ -55°C ≤ T_C ≤ +125°C +4.5 V ≤ VCC ≤ +5.5 V unless otherwise specified	V_{CC}	Group A subgroups	Limits 3/		Unit
					Min	Max	
Quiescent supply current delta, TTL input levels 3005	ΔI_{CC} 8/	One input at 3.4 V Other inputs at V_{CC} or GND	5.5 V	1, 2, 3		50.0	µA
Input capacitance 3012	C_{IN}	Control inputs T_C = +25°C see 4.4.1b	5.0 V	4		10.5	pF
I/O port capacitance	$C_{I/O}$	A or B ports T_C = +25°C see 4.4.1b	5.0 V	4		15.0	pF
Low level ground bounce noise	V_{OLP} 9/	V_{IH} = 3.0 V V_{IL} = 0.0 V T_A = +25°C See 4.4.1d See figure 4	5.0 V	4		2100	mV
	V_{OLV} 9/		5.0 V	4		-1450	mV
High level V_{CC} bounce noise	V_{OHP} 9/		5.0 V	4		1400	mV
	V_{OHV} 9/		5.0 V	4		-900	mV
Functional test 3014	10/	V_{IN} = 2.0 V or 0.8 V Verify output V_{OUT} See 4.4.1c	4.5 V	7, 8	L	H	
			5.5 V	7, 8	L	H	
Propagation delay time, An to Bn 3003	t_{PLH1} 11/	R_L = 500Ω C_L = 50 pF minimum See figure 5.	5.0 V	9	1.5	4.0	ns
			4.5 V and 5.5 V	10, 11	1.5	5.1	
	t_{PHL1} 11/		5.0 V	9	2.0	5.2	
			4.5 V and 5.5 V	10, 11	2.0	6.1	

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test conditions 2/ $-55°C \le T_C \le +125°C$ $+4.5\ V \le VCC \le +5.5\ V$ unless otherwise specified	V_{CC}	Group A subgroups	Limits 3/		Unit
					Min	Max	
Propagation delay time, Bn to An 3003	t_{PLH2} 11/	$R_L = 500\Omega$ $C_L = 50$ pF minimum See figure 5.	5.0 V	9	1.0	3.6	ns
			4.5 V and 5.5 V	10, 11	1.0	4.5	
	t_{PHL2} 11/		5.0 V	9	2.0	4.5	
			4.5 V and 5.5 V	10, 11	2.0	5.1	
Propagation delay time, LEBA to An 3003	t_{PLH3} 11/	$R_L = 500\Omega$ $C_L = 50$ pF minimum See figure 5.	5.0 V	9	2.0	4.5	ns
			4.5 V and 5.5 V	10, 11	2.0	5.6	
	t_{PHL3} 11/		5.0 V	9	2.0	4.7	
			4.5 V and 5.5 V	10, 11	2.0	5.4	
Propagation delay time, LEAB to Bn 3003	t_{PLH4} 11/	$R_L = 500\Omega$ $C_L = 50$ pF minimum See figure 5.	5.0 V	9	2.0	4.8	ns
			4.5 V and 5.5 V	10, 11	2.0	6.1	
	t_{PHL4} 11/		5.0 V	9	2.0	5.2	
			4.5 V and 5.5 V	10, 11	2.0	6.4	
Propagation delay time, CLKBA to An 3003	t_{PLH5} 11/	$R_L = 500\Omega$ $C_L = 50$ pF minimum See figure 5.	5.0 V	9	1.5	4.7	ns
			4.5 V and 5.5 V	10, 11	1.5	5.4	

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test conditions 2/ -55°C ≤ T_C ≤ +125°C +4.5 V ≤ VCC ≤ +5.5 V unless otherwise specified	V_{CC}	Group A subgroups	Limits 3/		Unit
					Min	Max	
Propagation delay time, CLKBA to An 3003	t_{PHL5} 11/	R_L = 500Ω C_L = 50 pF minimum See figure 5.	5.0 V	9	1.5	4.3	ns
			4.5 V and 5.5 V	10, 11	1.5	5.2	
Propagation delay time, CLKAB to Bn 3003	t_{PLH6} 11/	R_L = 500Ω C_L = 50 pF minimum See figure 5.	5.0 V	9	1.5	4.7	ns
			4.5 V and 5.5 V	10, 11	1.5	6.0	
	t_{PHL6} 11/		5.0 V	9	1.5	4.8	
			4.5 V and 5.5 V	10, 11	1.5	5.8	
Propagation delay time, output enable, $\overline{OEBA}$ to An 3003	t_{PZH1} 11/	R_L = 500 Ω C_L = 50 pF minimum See figure 5.	5.0 V	9	2.0	4.6	ns
			4.5 V and 5.5 V	10, 11	2.0	5.5	
	t_{PZL1} 11/		5.0 V	9	2.0	4.7	
			4.5 V and 5.5 V	10, 11	2.0	5.8	
Propagation delay time, output enable, $\overline{OEAB}$ to Bn 3003	t_{PZH2} 11/	R_L = 500Ω C_L = 50 pF minimum See figure 5.	5.0 V	9	2.0	5.3	ns
			4.5 V and 5.5 V	10, 11	1.5	6.6	
	t_{PZL2} 11/		5.0 V	9	2.0	5.1	
			4.5 V and 5.5 V	10, 11	2.0	6.2	

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test conditions 2/ -55°C ≤ T_C ≤ +125°C +4.5 V ≤ VCC ≤ +5.5 V unless otherwise specified	V_{CC}	Group A subgroups	Limits 3/		Unit
					Min	Max	
Propagation delay time, output disable, OEBA to An 3003	t_{PHZ1} 11/	R_L = 500Ω C_L = 50 pF minimum See figure 5.	5.0 V	9	2.0	5.4	ns
			4.5 V and 5.5 V	10, 11	1.4	6.6	
	t_{PLZ1} 11/		5.0 V	9	1.5	4.7	
			4.5 V and 5.5 V	10, 11	1.5	5.8	
Propagation delay time, output disable, OEAB to Bn 3003	t_{PZH2} 11/	R_L = 500Ω C_L = 50 pF minimum See figure 5.	5.0 V	9	2.0	4.8	ns
			4.5 V and 5.5 V	10, 11	1.4	5.6	
	t_{PZL2} 11/		5.0 V	9	1.5	4.5	
			4.5 V and 5.5 V	10, 11	1.5	5.7	
Maximum operating frequency	f_{max}	R_L = 500Ω C_L = 50 pF minimum See figure 5.	5.0 V	9	150		MHz
			4.5 V and 5.5 V	10,11	150		
Clock frequency	f_{clock}	R_L = 500Ω C_L = 50 pF minimum See figure 5.	4.5 V and 5.5 V	9,10,11	0.0	150	MHz
Pulse duration	t_w	LEAB or LEBA high	4.5 V and 5.5 V	9,10,11	2.5		ns
	12/	CLKAB or CLKBA high or low			3.3		

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test conditions 2/ -55°C ≤ T_C ≤ +125°C +4.5 V ≤ VCC ≤ +5.5 V unless otherwise specified	V_{CC}	Group A subgroups	Limits 3/		Unit
					Min	Max	
Setup time	t_s 12/	A before CLKAB↑ or B before CLKBA↑	4.5 V and 5.5 V	9,10,11	4.8		ns
		A before LEAB↓ or B before LEBA↓, CLK high			2.5		
		A before LEAB↓ or B before LEBA↓, CLK low			1.2		
		$\overline{\text{CLKENAB}}$ before CLKAB↑ or $\overline{\text{CLKENBA}}$ before CLKBA↑			2.7		
Hold time	t_h 12/	A after CLKAB↑ or B after CLKBA↑	4.5 V and 5.5 V	9,10,11	0.5		ns
		A after LEAB↓ or B after LEBA↓			2.0		
		$\overline{\text{CLKENAB}}$ after CLKAB↑ or $\overline{\text{CLKENBA}}$ after CLKBA↑			0.5		

1/ For tests not listed in the referenced MIL-STD-883 (e.g. ΔI_{CC}), utilize the general test procedure of 883 under the conditions listed herein.

2/ Each input/output, as applicable, shall be tested at the specified temperature, for the specified limits, to the tests in table I herein. Output terminals not designated shall be high level logic, low level logic, or open, except for all I_{CC} and ΔI_{CC} tests, where the output terminals shall be open. When performing these tests, the current meter shall be placed in the circuit such that all current flows through the meter. For input terminals not designated, V_{IN} = GND or $V_{IN} \geq$ 3.0 V.

3/ For negative and positive voltage and current values, the sign designates the potential difference in reference to GND and the direction of current flow, respectively; and the absolute value of the magnitude, not the sign, is relative to the minimum and maximum limits, as applicable, listed herein. All devices shall meet or exceed the limits specified in Table I at 4.5 V ≤ V_{CC} ≤ 5.5 V.

4/ For I /O ports, the limit includes I_{OZH} or I_{OZL} leakage current from the output circuitry.

5/ This parameter is characterized, but not production tested.

6/ For I /O ports, the limit includes I_{IH} or I_{IL} leakage current from the input circuitry.

7/ Not more than one output should be tested at one time, and the duration of the test condition should not exceed one second.

8/ This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather than at 0.0 V or V_{CC}. This test may be performed either one input at a time (preferred method) or with all input pins simultaneously at VIN = VCC - 2.1 V (alternate method). Classes Q and V shall use the preferred method. When the test is performed using the alternate test method, the maximum limit is equal to the number of inputs at a high TTL input level times 1.5 mA, and the preferred method and limits are guaranteed.

9/ This test is for qualification only. Ground and V_{CC} bounce tests are performed on a non-switching (quiescent) output and are used to measure the magnitude of induced noise caused by other simultaneously switching outputs. The test is performed on a low noise bench test fixture. For the device under test, all outputs shall be loaded with 500 Ω of load resistance and a minimum of 50 pF of load capacitance (see figure 4). Only chip capacitors and resistors shall be used. The output load components shall be located as close as possible to the device outputs. It is suggested, that whenever possible, this distance be kept to less than 0.25 inches. Decoupling capacitors shall be placed in parallel from V_{CC} to ground. The values of these decoupling capacitors shall be determined by the device manufacturer. The low and high level ground and V_{CC} bounce noise is measured at the quiet output using a 1 GHz minimum bandwidth oscilloscope with a 50Ω input impedance.

The output load components shall be located as close as possible to the device outputs. It is suggested, that whenever possible, this distance be kept to less than 0.25 inches. Decoupling capacitors shall be placed in parallel from V_{CC} to ground. The values of these decoupling capacitors shall be determined by the device manufacturer. The low and high level ground and V_{CC} bounce noise is measured at the quiet output using a 1 GHz minimum bandwidth oscilloscope with a 50 Ω input impedance.

The device inputs shall be conditioned such that all outputs are at a high nominal V_{OH} level. The device inputs shall then be conditioned such that they switch simultaneously and the output under test remains at V_{OH} as all other outputs possible are switched from V_{OH} to V_{OL}. V_{OHV} and V_{OHP} are then measured from the nominal V_{OH} level to the largest negative and positive peaks, respectively (see figure 4). This is then repeated with the same outputs not under test switching from V_{OL} to V_{OH}.

The device inputs shall be conditioned such that all outputs are at a low nominal V_{OL} level. The device inputs shall then be conditioned such that they switch simultaneously and the output under test remains at V_{OL} as all other outputs possible are switched from V_{OL} to V_{OH}. V_{OLP} and V_{OLV} are then measured from the nominal V_{OL} level to the largest positive and negative peaks, respectively (see figure 4). This is then repeated with the same outputs not under test switching from V_{OH} to V_{OL}.

10/ Tests shall be performed in sequence, attributes data only. Functional tests shall include the truth table and other logic patterns used for fault detection. The test vectors used to verify the truth table shall, at a minimum, test all functions of each input and output. All possible input to output logic patterns per function shall be guaranteed, if not tested, to the truth table in figure 2 herein. Functional tests shall be performed in sequence as approved by the qualifying activity on qualified devices. After incorporating allowable tolerances per MIL-STD-883, V_{IL} = 0.4 V and V_{IH} = 2.4 V. For outputs, L ≤ 0.8 V, H ≥ 2.0 V.

11/ For propagation delay tests, all paths must be tested.

12/ This parameter shall be guaranteed, if not tested, to the limits specified in table I herein.

Device	01		
Case Outlines	X		
Terminal Number	Terminal Symbol	Terminal number	Terminal Symbol
1	$\overline{OEAB}$	29	$\overline{CLKENBA}$
2	LEAB	30	CLKBA
3	A1	31	B18
4	GND	32	GND
5	A2	33	B17
6	A3	34	B16
7	V_{CC}	35	V_{CC}
8	A4	36	B15
9	A5	37	B14
10	A6	38	B13
11	GND	39	GND
12	A7	40	B12
13	A8	41	B11
14	A9	42	B10
15	A10	43	B9
16	A11	44	B8
17	A12	45	B7
18	GND	46	GND
19	A13	47	B6
20	A14	48	B5
21	A15	49	B4
22	V_{CC}	50	V_{CC}
23	A16	51	B3
24	A17	52	B2
25	GND	53	GND
26	A18	54	B1
27	OEBA	55	$\overline{CLKAB}$
28	LEBA	56	CLKENAB

Terminal descriptions	
Terminal symbol	Description
An (n = 1 to 18)	Data inputs / outputs, A port
Bn (n = 1 to 18)	Data inputs / outputs, B port
LEAB, LEBA	A to B / B to A latch enable control inputs
$\overline{OEAB}$, $\overline{OEBA}$	A to B / B to A output enable control inputs
CLKAB, CLKBA	A to B / B to A clock inputs
$\overline{CLKENAB}$, $\overline{CLKENBA}$	A to B / B to A clock enable inputs

FIGURE 1. Terminal connections.

INPUTS 1/					OUTPUT
$\overline{CLKENAB}$	$\overline{OEAB}$	LEAB	CLKAB	An	Bn
X	H	X	X	X	Z
X	L	H	X	L	L
X	L	H	X	H	H
H	L	L	X	X	B_0 2/
H	L	L	X	X	B_0 2/
L	L	L	↑	L	L
L	L	L	↑	H	H
L	L	L	L	X	B_0 2/
L	L	L	H	X	B_0 3/

1/ - A - to - B data flow is shown; B - to - A data flow is the same, except using $\overline{OEBA}$, LEBA, CLKBA AND $\overline{CLKENBA}$.
2/ - The output level before the indicated steady-state input conditions were established.
3/ - The output level before the indicated steady-state input conditions were established, provided that CLKAB was Low before LEAB went Low.

H = High voltage level.
L = Low voltage level.
X = Irrelevant.
Z = High impedance.
↑ = Low - to - high clock transition.

FIGURE 2. Truth table.

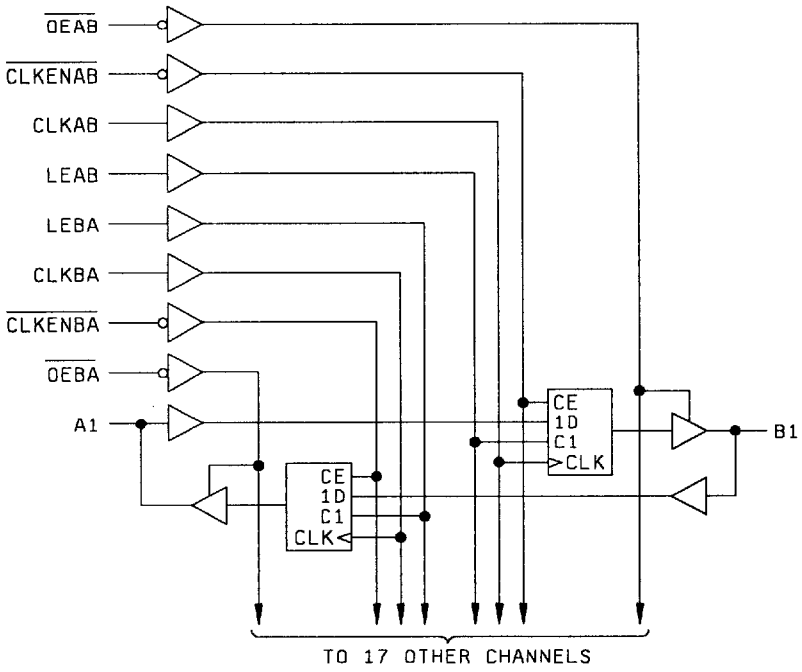
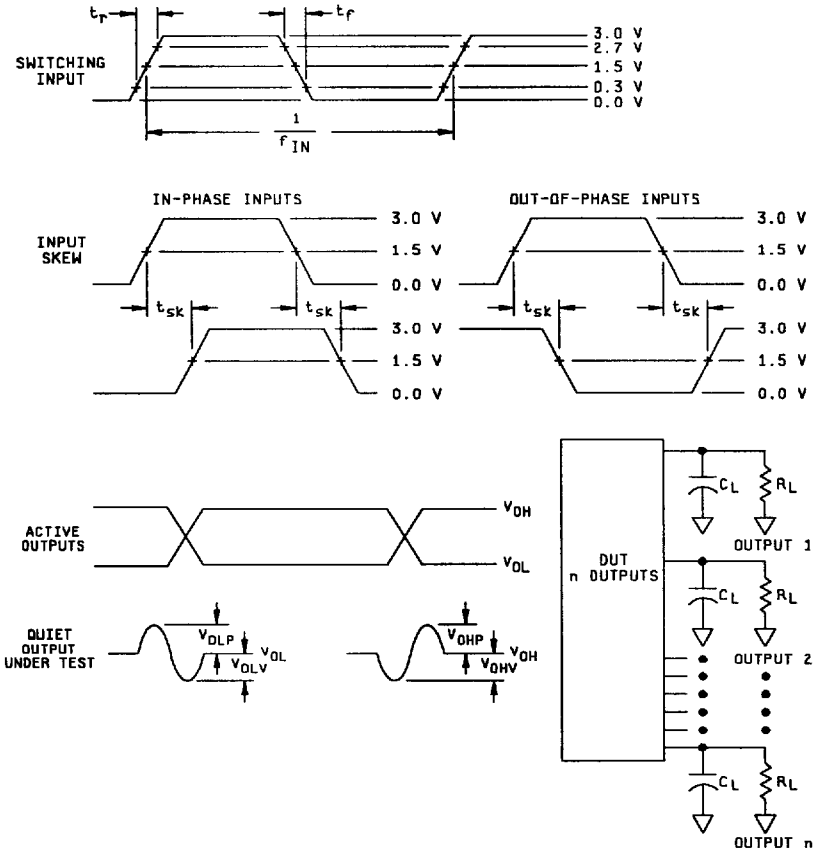


FIGURE 3. Logic diagram.



NOTES:
1. C_L includes a 47 pF chip capacitor (-0 percent, +20 percent) and at least 3 pF of equivalent capacitance from the test jig and probe.
2. $R_L = 450\Omega \pm 1$ percent, chip resistor in series with a 50Ω termination. For monitored outputs, the 50Ω termination shall be the 50Ω characteristic impedance of the coaxial connector to the oscilloscope.
3. Input signal to the device under test:
   a. V_{IN} = 0.0 V to 3.0 V; duty cycle = 50 percent; $f_{IN} \geq 1$ MHz.
   b. t_r, t_f = 3.0 ns ±1.0 ns. For input signal generators incapable of maintaining these values of t_r and t_f, the 3.0 ns limit may be increased up to 10 ns, as needed, maintaining the ±1.0 ns tolerance and guaranteeing the results at 3.0 ns ±1.0 ns; skew between any two switching inputs signals (t_{sk}): ≤ 250 ps.

FIGURE 4. Ground bounce test circuit and waveforms.

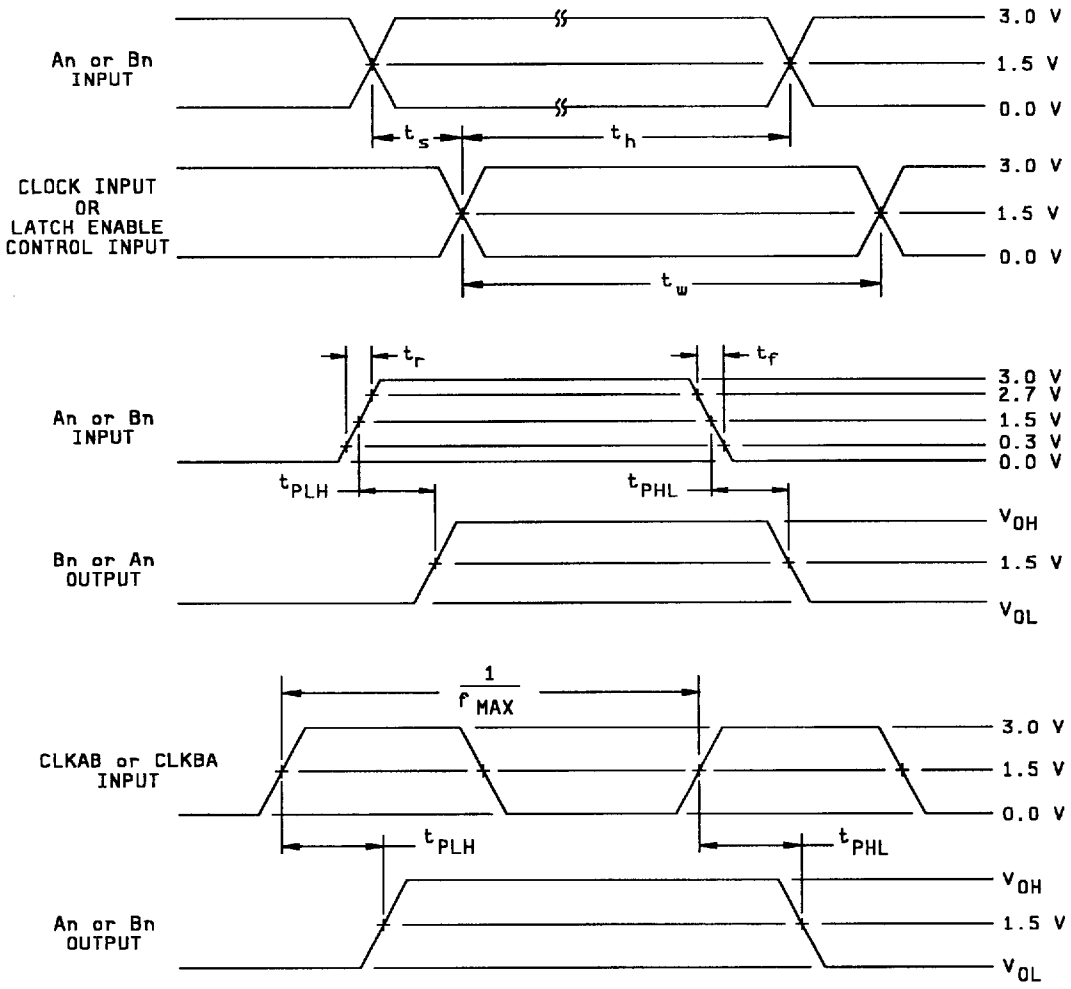
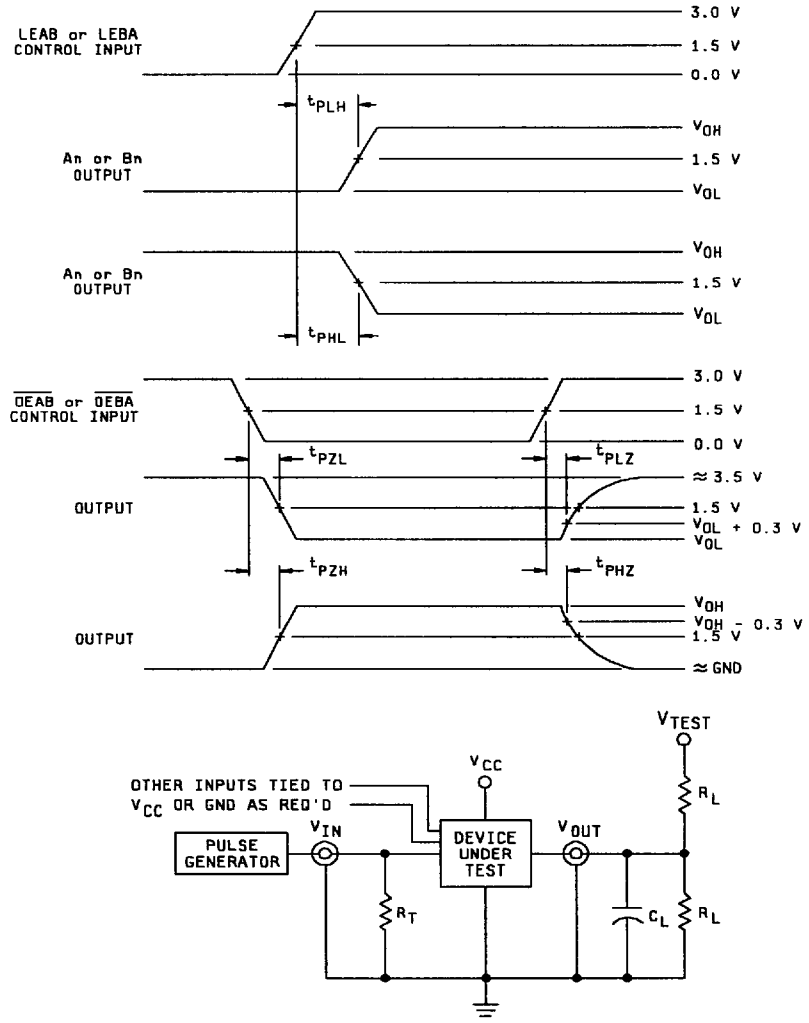


FIGURE 5. Switching waveforms and test circuit.



NOTES:

1. When measuring t_{PLZ} and t_{PZL}: V_{TEST} = 7.0 V.
2. When measuring t_{PHZ} , t_{PZH}, t_{PLH} and t_{PHL}: V_{TEST} = Open
3. The t_{PZL} and t_{PLZ} reference waveform is for the output under test with internal conditions such that the output is at V_{OL} except when disabled by the output enable control. The t_{PZH} and t_{PHZ} reference waveform is for the output under test with internal conditions such that the output is at V_{OH} except when disabled by the output enable control.
4. C_L 50 pF (includes test jig and probe capacitance).
5. R_T = 50Ω or equivalent.
6. R_L = 500Ω or equivalent.
7. Input signal from pulse generator: V_{IN} = 0.0 V to 3.0 V; PRR ≤ 10 MHz; t_r = 2.5 ns; t_f = 2.5 ns; t_r and t_f shall be measured from 2.7 V to 0.3 V and from 0.3 V to 2.7 V, respectively; duty cycle = 50 percent.
8. Timing parameters shall be tested at a minimum input frequency of 1 MHz.
9. The outputs are measured one at a time with one transition per measurement.

FIGURE 5. Switching waveforms and test circuit - Continued.

4. QUALITY ASSURANCE PROVISIONS

4.1 Sampling and inspection. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.

4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.

4.2.1 Additional criteria for device class M.

a. Burn-in test, method 1015 of MIL-STD-883.

(1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.

(2) T_A = +125°C, minimum.

b. Interim and final electrical test parameters shall be as specified in table II herein.

4.2.2 Additional criteria for device classes Q and V.

a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.

b. Interim and final electrical test parameters shall be as specified in table II herein.

c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.3.1 Electrostatic discharge sensitivity qualification inspection. Electrostatic discharge sensitivity (ESDS) testing shall be performed in accordance with MIL-STD-883, method 3015. ESDS testing shall be measured only for initial qualification and after process or design changes which may affect ESDS classification.

4.4 Conformance inspection. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-PRF-38535 permits alternate in-line control testing. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

TABLE II. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	- - -	- - -	1
Final electrical parameters (see 4.2)	1/ 1, 2, 3, 7, 8, 9, 10, 11	1/ 1, 2, 3, 7, 8, 9, 10, 11	2/ 1, 2, 3, 7, 8, 9, 10, 11
Group A test requirements (see 4.4)	1, 2, 3, 4, 7, 8, 9, 10, 11	1, 2, 3, 4, 7, 8, 9, 10, 11	1, 2, 3, 4, 7, 8, 9, 10, 11
Group C end-point electrical parameters (see 4.4)	1, 2, 3	1, 2, 3	1, 2, 3, 7,8, 9, 10, 11
Group D end-point electrical parameters (see 4.4)	1, 2, 3	1, 2, 3	1, 2, 3
Group E end-point electrical parameters (see 4.4)	1, 7, 9	1, 7, 9	1, 7, 9

1/ PDA applies to subgroup 1.
2/ PDA applies to subgroups 1 and 7.

4.4.1 Group A inspection.

a. Tests shall be as specified in table II herein.

b. For device class M, subgroups 7 and 8 tests shall be sufficient to verify the truth table in figure 2 herein. The test vectors used to verify the truth table shall, at a minimum, test all functions of each input and output. All possible input to output logic patterns per function shall be guaranteed, if not tested, to the truth table in figure 2, herein. For device classes Q and V, subgroups 7 and 8 shall include verifying the functionality of the device.

c. C_{IN}, and $C_{I/O}$ shall be measured only for initial qualification and after process or design changes which may affect capacitance. C_{IN} and $C_{I/O}$ shall be measured between the designated terminal and GND at a frequency of 1 MHz. This test may be performed at 10 MHz and guaranteed, if not tested, at 1 MHz. The DC bias for the pin under test (V_{BIAS}) = 2.5 V or 3.0 V. For C_{IN} and $C_{I/O}$ test all applicable pins on five devices with zero failures.

For C_{IN} a device manufacturer may qualify devices by functional groups. A specific functional group shall be composed of function types, that by design, will yield the same capacitance values when tested in accordance with table I, herein. The device manufacturer shall set a function group limit for the C_{IN} and $C_{I/O}$ tests. The device manufacturer may then test one device functional group, to the limits and conditions specified herein. All other device functions in that particular functional group shall be guaranteed, if not tested, to the limits and test conditions specified in table I, herein. The device manufacturers shall submit to DSCC-VA the device functions listed in each functional group and the test results for each device tested.

d. Ground and V_{CC} bounce tests are required for all device classes. These tests shall be performed only for initial qualification, after process or design changes which may affect the performance of the device, and any changes to the test fixture. V_{OLP}, V_{OLV}, V_{OHP}, and V_{OHV} shall be measured for the worst case outputs of the device. All other outputs shall be guaranteed, if not tested, to the limits established for the worst case outputs. The worst case outputs tested are to be determined by the manufacturer. Test 5 devices assembled in the worst case package type supplied to this document. All other package types shall be guaranteed, if not tested, to the limits established for the worst case package. The 5 devices to be tested shall be the worst case device type supplied to this drawing. All other device types shall be guaranteed, if not tested, to the limits established for the worst case device type. The package type and device type to be tested shall be determined by the manufacturer. The device manufacturer will submit to DSCC-VA data that shall include all measured peak values for each device tested and detailed oscilloscope plots for each V_{OLP}, V_{OLV}, V_{OHP}, and V_{OHV} from one sample part per function. The plot shall contain the waveforms of both a switching output and the output under test.

Each device manufacturer shall test product on the fixtures they currently use. When a new fixture is used, the device manufacturer shall inform DSCC-VA of this change and test the 5 devices on both the new and old test fixtures. The device manufacturer shall then submit to DSCC-VA data from testing on both fixtures, that shall include all measured peak values for each device tested and detailed oscilloscope plots for each V_{OLP}, V_{OLV}, V_{OHP}, and V_{OHV} from one sample part per function. The plot shall contain the waveforms of both a switching output and the output under test.

For V_{OHP}, V_{OHV}, V_{OLP}, and V_{OLV}, a device manufacturer may qualify devices by functional groups. A specific functional group shall be composed of function types, that by design, will yield the same test values when tested in accordance with table I, herein. The device manufacturer shall set a functional group limit for the V_{OHP}, V_{OHV}, V_{OLP}, and V_{OLV} tests. The device manufacturer may then test one device function from a functional group, to the limits and conditions specified herein. All other device functions in that particular functional group shall be guaranteed, if not tested, to the limits and conditions specified in table I, herein. The device manufacturers shall submit to DSCC-VA the device functions listed in each functional group and test results, along with the oscilloscope plots, for each device tested.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table II herein.

4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:

a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.

b. T_A = +125°C, minimum.

c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specifie d in test method 1005 of MIL-STD-883.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table II herein.

4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

a. End-point electrical parameters shall be as specified in table II herein.

b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C ±5°C, after exposure, to the subgroups specified in table II herein.

c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.

4.5 Methods of inspection. Methods of inspection shall be specified as follows:

4.5.1 Voltage and current. Unless otherwise specified, all voltages given are referenced to the microcircuit GND terminal. Currents given are conventional current and positive when flowing into the referenced terminal.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.

6.1.2 Substitutability. Device class Q devices will replace device class M devices.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-973 using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users should inform Defense Supply Center Columbus when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0674.

6.4 Comments. Comments on this drawing should be directed to DSCC-VA , Columbus, Ohio 43216-5000, or telephone (614) 692-0674.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.

6.6.2 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

STANDARD MICROCIRCUIT DRAWING SOURCE APPROVAL BULLETIN
DATE: 98-06-24

Approved sources of supply for SMD 5962-98593 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535.

Standard microcircuit drawing PIN 1/	Vendor CAGE number	Vendor similar PIN 2/
5962-9859301QXA	01295	SNJ54ABT162601WD

1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the Vendor to determine its availability.

2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE number	Vendor name and address
01295	Texas Instruments Incorporated 13500 N. Central Expressway P.O. Box 655303 Dallas, TX 75265 Point of contact: I-20 at FM 1788 Midland, TX 79711-0448

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.